

This Listing of Claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1. (Currently Amended) A nonvolatile semiconductor memory device comprising:
  - a memory array ~~composed of~~ comprising a plurality of floating-gate field-effect ~~transistor~~ transistors ~~connected to a row line and a column line and~~ disposed in a matrix configuration, the transistors being connected to corresponding row lines and column lines, at least one of the transistors comprising the floating-gate field-effect transistor including
  - a source and a drain which are formed inside a P-type well ~~provided~~ formed inside an N-type well formed on a semiconductor substrate,
  - a floating gate formed ~~[[over]]~~ above a portion of the semiconductor substrate between the source and the drain with an insulating film interposed ~~therebetween~~ between the floating gate and said portion of the semiconductor substrate, and
  - a control gate formed on the floating gate with ~~[[a]]~~ another insulating film interposed therebetween;
  - a first voltage application means for circuit applying a first voltage to the P-type well when an erasing pulse is applied; and
  - a second voltage application means for circuit applying a second voltage to the N-type well when ~~[[an]]~~ the erasing pulse is applied.

2. (Currently Amended) The nonvolatile semiconductor memory device ~~as defined in Claim of claim~~ 1, wherein the first voltage and the second voltage are positive voltages, and the second voltage is higher than the first voltage.

3. (Currently Amended) The nonvolatile semiconductor memory device ~~as defined in Claim of claim~~ 1, wherein the first voltage application ~~means is~~ circuit comprises a first high-voltage pumping circuit for generating the first voltage, and the second voltage application ~~means is~~ circuit comprises a second high-voltage pumping circuit for generating the second voltage.

4. (Currently Amended) The nonvolatile semiconductor memory device ~~as defined in Claim of claim~~ 1, wherein the first voltage application ~~means is~~ circuit comprises a first high-voltage pumping circuit for generating the first voltage, and the second voltage application ~~means is~~ circuit comprises an auxiliary pumping circuit for ~~generating the second voltage higher than raising the first voltage by receiving to generate the first second~~ voltage.

5. (Currently Amended) The nonvolatile semiconductor memory device ~~as defined in Claim of claim~~ 1, wherein the second voltage application ~~means is~~ circuit comprises a high-voltage pumping circuit for generating the second voltage ~~higher than the first voltage~~, and the first voltage application ~~means is~~ circuit comprises a regulator circuit for ~~generating the first voltage lower than lowering the second voltage by receiving to generate the second first~~ voltage.